

# ZXMD63C03X

## 30V DUAL N AND P-CANNEL ENHANCEMENT MODE MOSFET

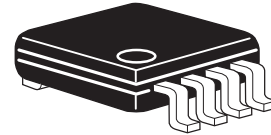
### SUMMARY

**N-CHANNEL:**  $V_{(BR)DSS}=30V$ ;  $R_{DS(ON)}=0.135\Omega$ ;  $I_D=2.3A$

**P-CHANNEL:**  $V_{(BR)DSS}=-30V$ ;  $R_{DS(ON)}=0.185\Omega$ ;  $I_D=-2.0A$

### DESCRIPTION

This new generation of high density MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



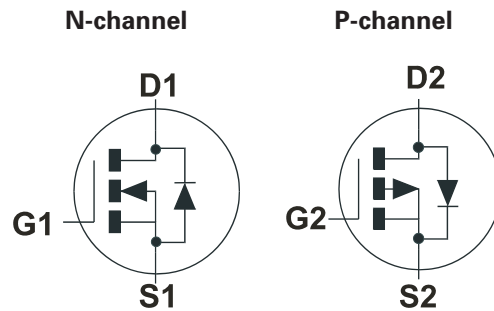
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### FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

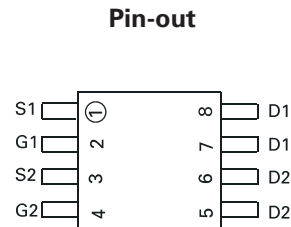
### APPLICATIONS

- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control



### ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXMD63C03XTA	7	12 embossed	1,000
ZXMD63C03XTC	13	12 embossed	4,000



Top view

### DEVICE MARKING

ZXM63C03

# ZXMD63C03X

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Drain-Source Voltage	$V_{DSS}$	30	-30	V
Gate- Source Voltage	$V_{GS}$	$\pm 20$		V
Continuous Drain Current ( $V_{GS}=4.5V$ ; $T_A=25^\circ C$ )(b)(d) ( $V_{GS}=4.5V$ ; $T_A=70^\circ C$ )(b)(d)	$I_D$	2.3	-2.0	A
		1.8	-1.6	A
Pulsed Drain Current (c)(d)	$I_{DM}$	14	-9.6	A
Continuous Source Current (Body Diode)(b)(d)	$I_S$	1.5	-1.4	A
Pulsed Source Current (Body Diode)(c)(d)	$I_{SM}$	14	-9.6	A
Power Dissipation at $T_A=25^\circ C$ (a)(d) Linear Derating Factor	$P_D$	0.87		W
		6.9		mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (a)(e) Linear Derating Factor	$P_D$	1.04		W
		8.3		mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b)(d) Linear Derating Factor	$P_D$	1.25		W
		10		mW/ $^\circ C$
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150		$^\circ C$

## THERMAL RESISTANCE

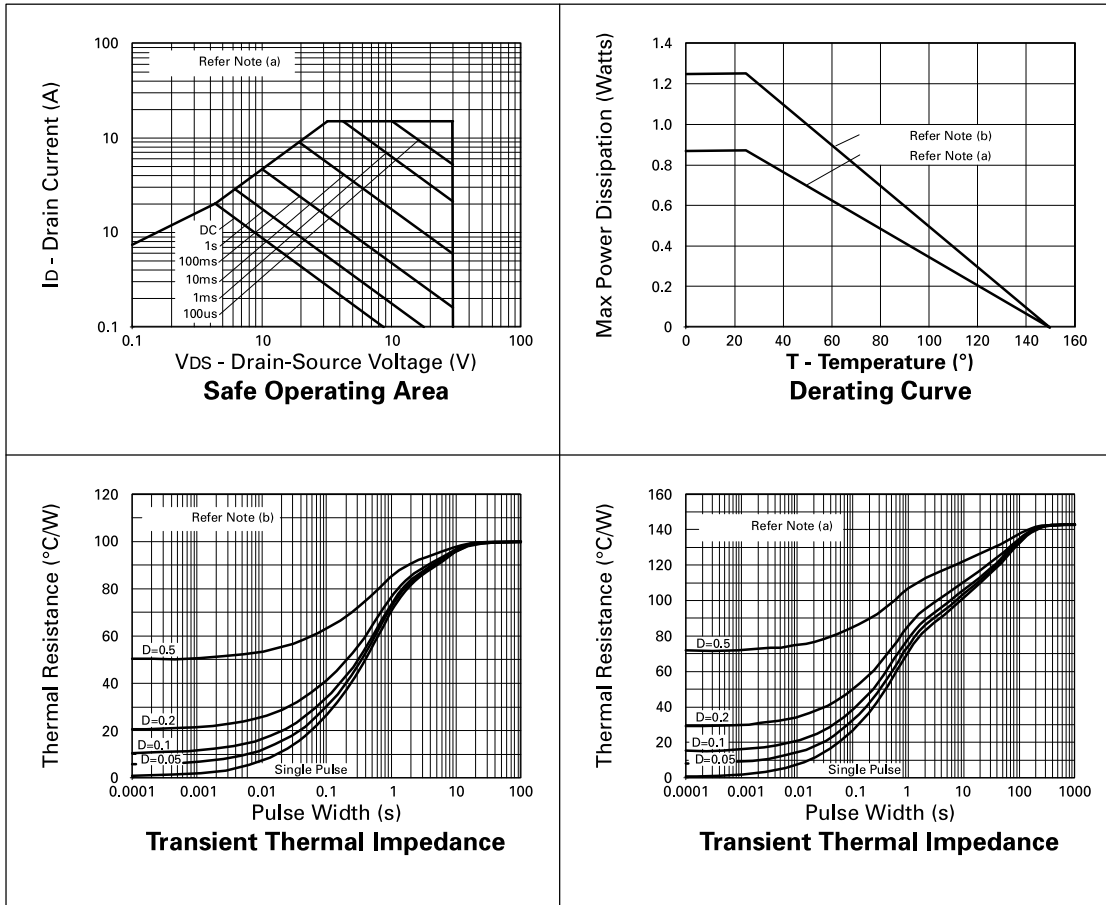
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(d)	$R_{\theta JA}$	143	$^\circ C/W$
Junction to Ambient (b)(d)	$R_{\theta JA}$	100	$^\circ C/W$
Junction to Ambient (a)(e)	$R_{\theta JA}$	120	$^\circ C/W$

### NOTES:

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
- (b) For a device surface mounted on FR4 PCB measured at  $t \leq 10$  secs.
- (c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
- (d) For device with one active die.
- (e) For device with two active die running at equal power.

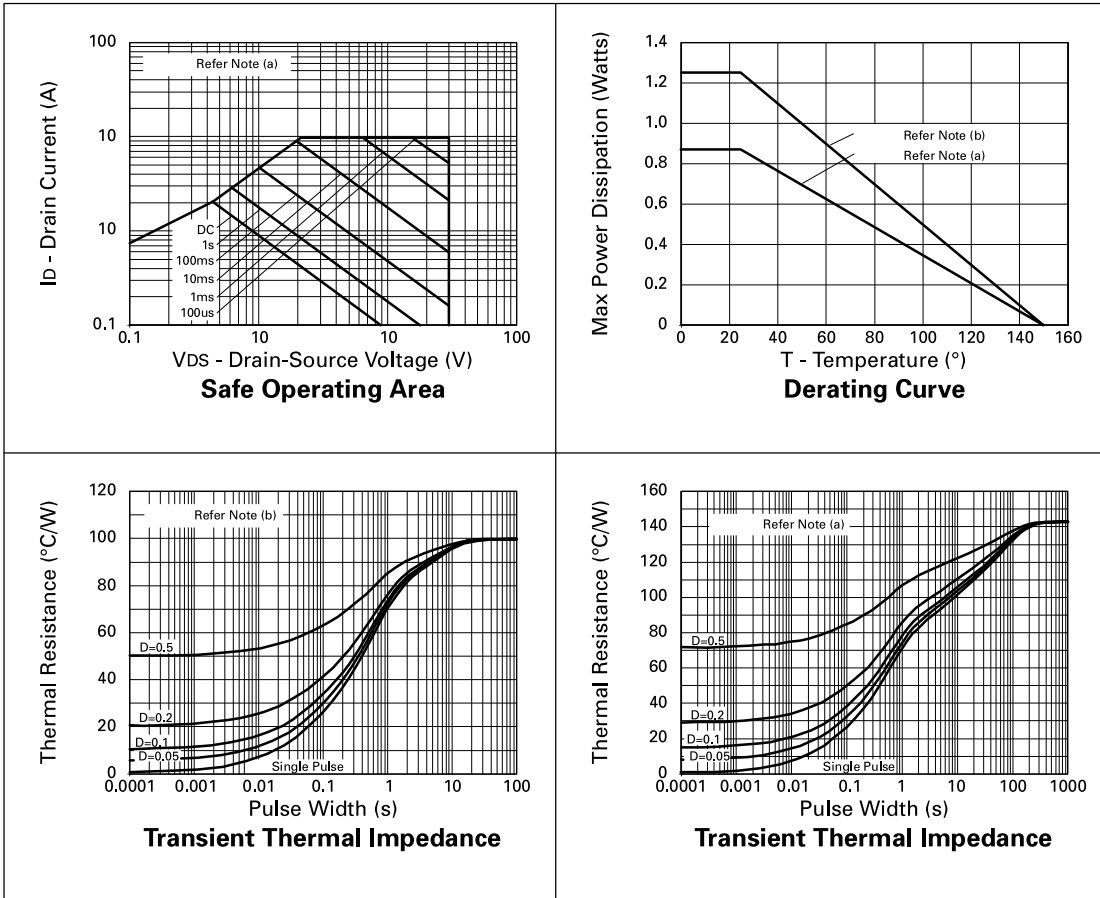
# ZXMD63C03X

## N-CHANNEL CHARACTERISTICS



# ZXMD63C03X

## P-CHANNEL CHARACTERISTICS



# ZXMD63C03X

## N-CHANNEL ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

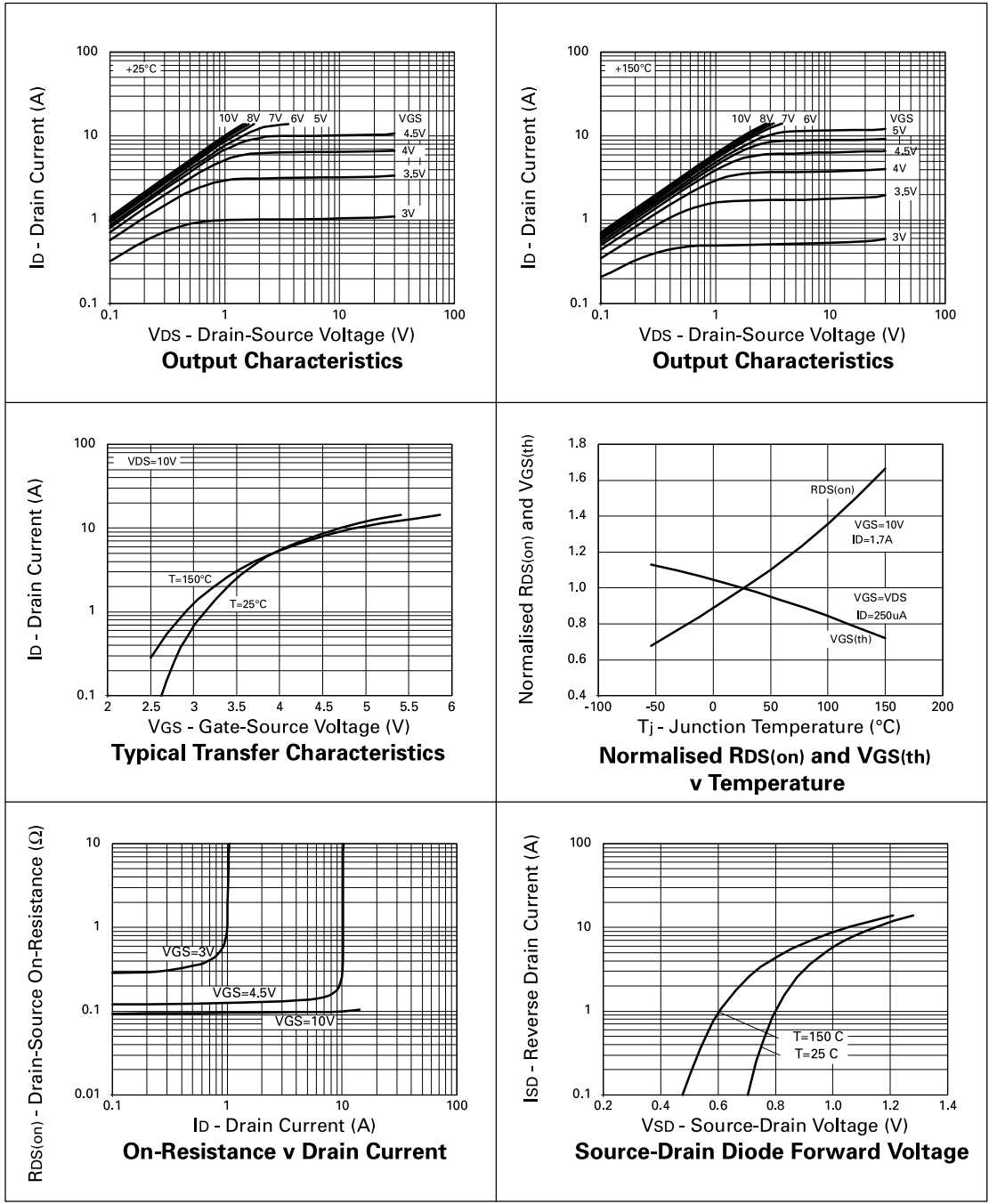
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	30			V	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$
Gate-Body Leakage	$I_{GSS}$			100	nA	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1.0			V	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.135 0.200	$\Omega$	$V_{GS}=10\text{V}, I_D=1.7\text{A}$ $V_{GS}=4.5\text{V}, I_D=0.85\text{A}$
Forward Transconductance (3)	$g_{fs}$	1.9			S	$V_{DS}=10\text{V}, I_D=0.85\text{A}$
<b>DYNAMIC (3)</b>						
Input Capacitance	$C_{iss}$		290		pF	$V_{DS}=25\text{V}, V_{GS}=0\text{V},$ $f=1\text{MHz}$
Output Capacitance	$C_{oss}$		70		pF	
Reverse Transfer Capacitance	$C_{rss}$		20		pF	
<b>SWITCHING(2) (3)</b>						
Turn-On Delay Time	$t_{d(on)}$		2.5		ns	$V_{DD}=15\text{V}, I_D=1.7\text{A}$ $R_G=6.1\Omega, R_D=8.7\Omega$ (Refer to test circuit)
Rise Time	$t_r$		4.1		ns	
Turn-Off Delay Time	$t_{d(off)}$		9.6		ns	
Fall Time	$t_f$		4.4		ns	
Total Gate Charge	$Q_g$			8	nC	$V_{DS}=24\text{V}, V_{GS}=10\text{V},$ $I_D=1.7\text{A}$ (Refer to test circuit)
Gate-Source Charge	$Q_{gs}$			1.2	nC	
Gate Drain Charge	$Q_{gd}$			2	nC	
<b>SOURCE-DRAIN DIODE</b>						
Diode Forward Voltage (1)	$V_{SD}$			0.95	V	$T_j=25^{\circ}\text{C}, I_S=1.7\text{A},$ $V_{GS}=0\text{V}$
Reverse Recovery Time (3)	$t_{rr}$		16.9		ns	$T_j=25^{\circ}\text{C}, I_F=1.7\text{A},$ $di/dt=100\text{A}/\mu\text{s}$
Reverse Recovery Charge(3)	$Q_{rr}$		9.5		nC	

### NOTES:

- (1) Measured under pulsed conditions. Width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$ .
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.

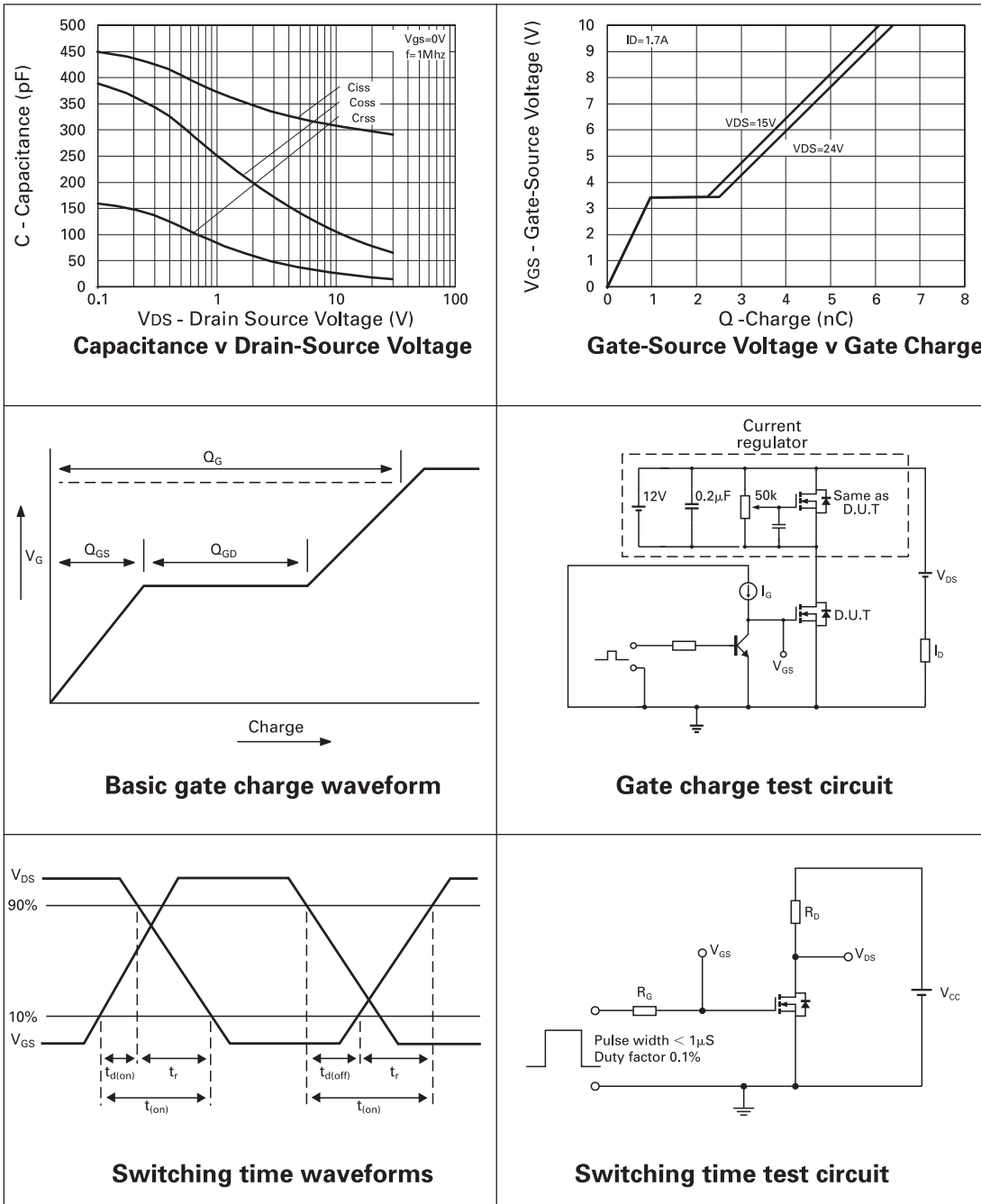
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## N-CHANNEL TYPICAL CHARACTERISTICS



# ZXMD63C03X

## N-CHANNEL CHARACTERISTICS



# ZXMD63C03X

## P-CHANNEL ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30			V	$I_D = -250\mu\text{A}$ , $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$			-1	$\mu\text{A}$	$V_{DS} = -30\text{V}$ , $V_{GS} = 0\text{V}$
Gate-Body Leakage	$I_{GSS}$			$\pm 100$	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	$I_D = -250\mu\text{A}$ , $V_{DS} = V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.185 0.27	$\Omega$ $\Omega$	$V_{GS} = -10\text{V}$ , $I_D = -1.2\text{A}$ $V_{GS} = -4.5\text{V}$ , $I_D = -0.6\text{A}$
Forward Transconductance (3)	$g_{fs}$	0.92			S	$V_{DS} = -10\text{V}$ , $I_D = -0.6\text{A}$
<b>DYNAMIC (3)</b>						
Input Capacitance	$C_{iss}$		270		pF	$V_{DS} = -25\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$
Output Capacitance	$C_{oss}$		80		pF	
Reverse Transfer Capacitance	$C_{rss}$		30		pF	
<b>SWITCHING(2) (3)</b>						
Turn-On Delay Time	$t_{d(on)}$		2.6		ns	$V_{DD} = -15\text{V}$ , $I_D = -1.2\text{A}$ $R_G = 6.2\Omega$ , $R_D = 6.2\Omega$ (Refer to test circuit)
Rise Time	$t_r$		4.8		ns	
Turn-Off Delay Time	$t_{d(off)}$		13.1		ns	
Fall Time	$t_f$		9.3		ns	
Total Gate Charge	$Q_g$			7	nC	$V_{DS} = -24\text{V}$ , $V_{GS} = -10\text{V}$ , $I_D = -1.2\text{A}$ (Refer to test circuit)
Gate-Source Charge	$Q_{gs}$			1.2	nC	
Gate Drain Charge	$Q_{gd}$			2	nC	
<b>SOURCE-DRAIN DIODE</b>						
Diode Forward Voltage (1)	$V_{SD}$			-0.95	V	$T_j = 25^{\circ}\text{C}$ , $I_S = -1.2\text{A}$ , $V_{GS} = 0\text{V}$
Reverse Recovery Time (3)	$t_{rr}$		21.4		ns	$T_j = 25^{\circ}\text{C}$ , $I_F = -1.2\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge(3)	$Q_{rr}$		15.7		nC	

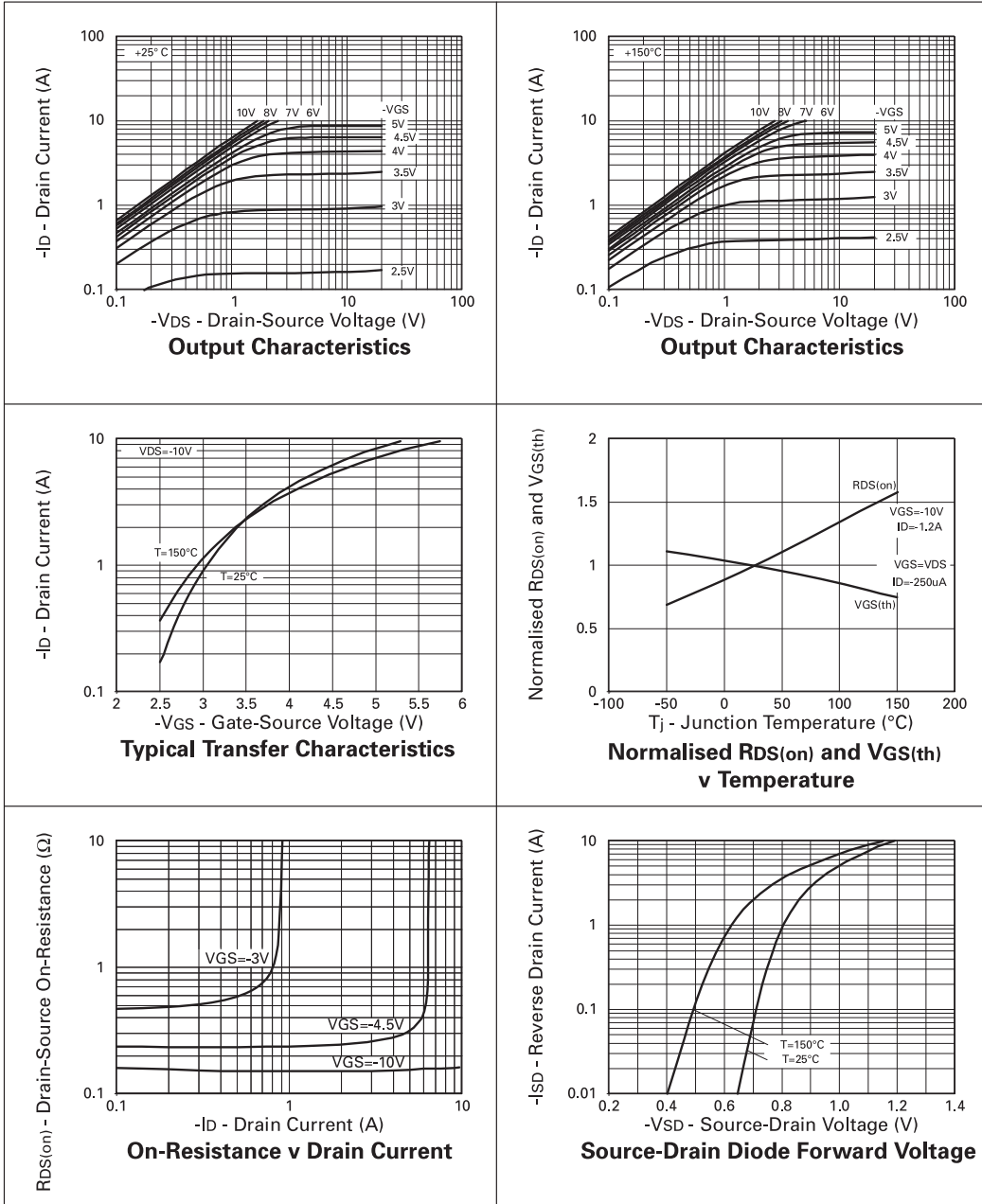
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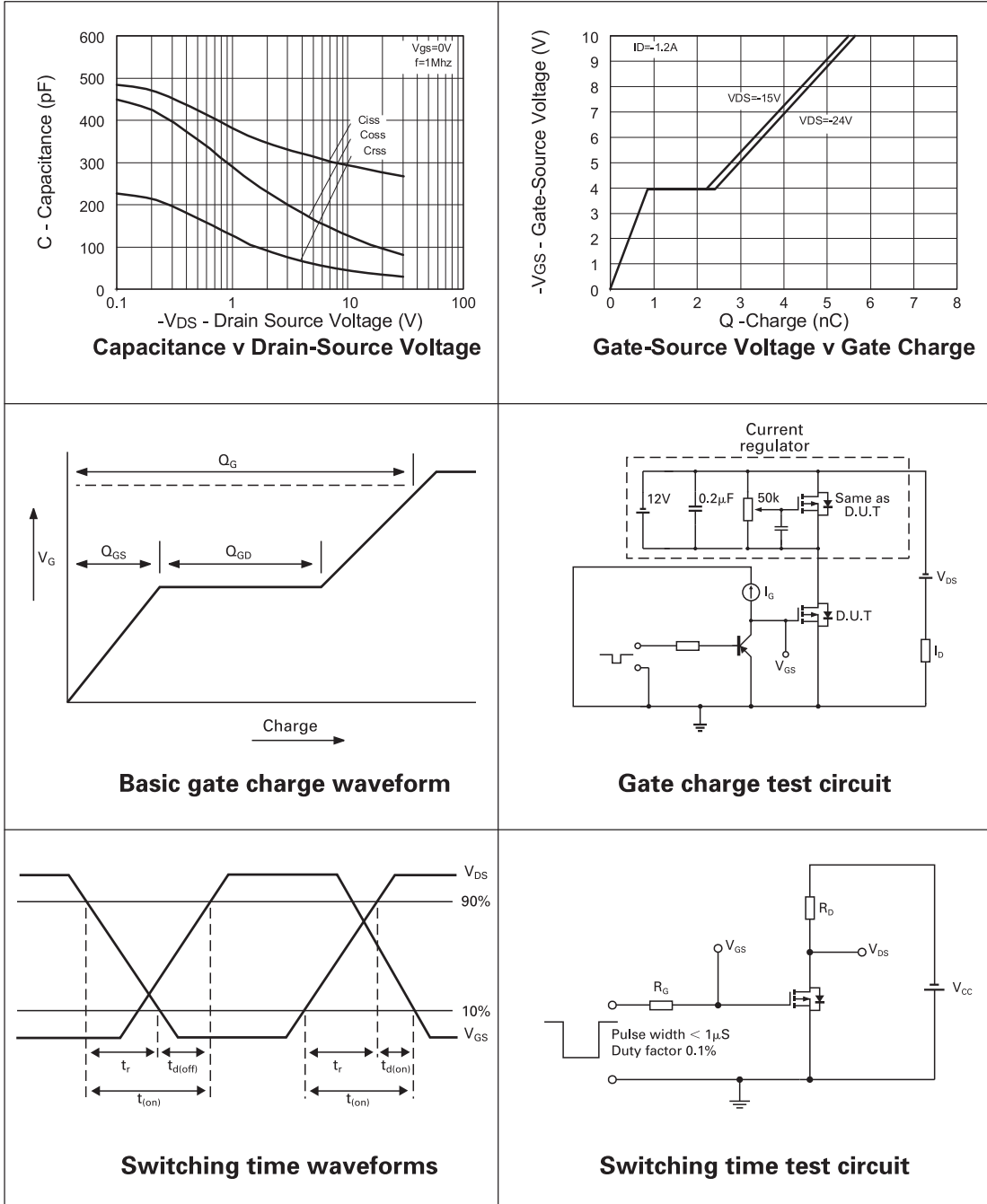
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## P-CHANNEL CHARACTERISTICS



# ZXMD63C03X

## P-CHANNEL TYPICAL CHARACTERISTICS



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"Preview"Future device intended for production at some point. Samples may be available

"Active"Product status recommended for new designs

"Last time buy (LTB)"Device will be discontinued and last time buy period and delivery is in effect

"Not recommended for new designs"Device is still in production to support existing designs and production

"Obsolete"Production has been discontinued

Datasheet status key:

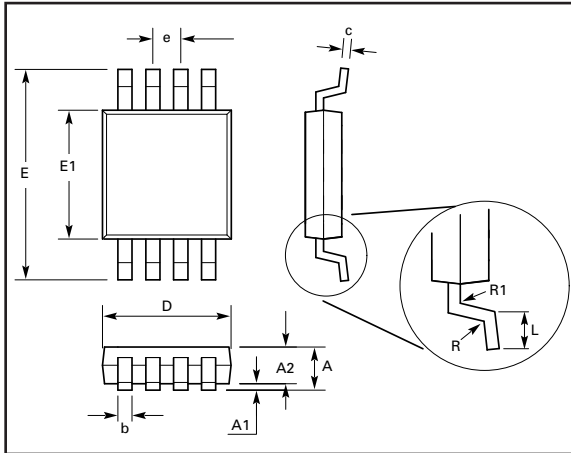
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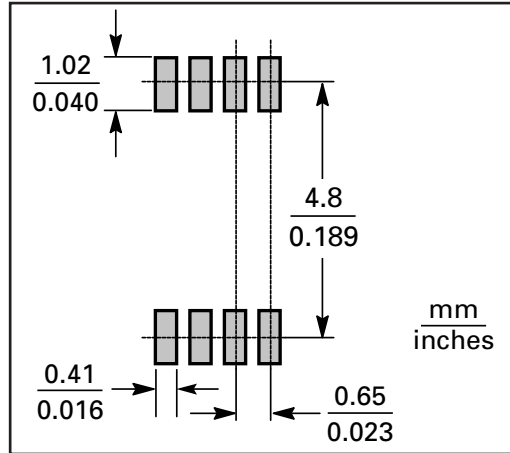
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## PACKAGE DIMENSIONS



## PAD LAYOUT DETAILS



DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	-	1.10	-	0.0433
A1	0.05	0.15	0.002	0.006
A2	0.75	0.95	0.0295	0.0374
b	0.25	0.40	0.010	0.0157
c	0.13	0.23	0.005	0.009
D	2.90	3.10	0.114	0.122
E	4.90 BSC		0.193 BSC	
E1	2.90	3.10	0.114	0.122
e	0.65 BSC		0.025 BSC	
L	0.40	0.70	0.0157	0.0192
R	0.07	-	0.0027	-
R1	0.07	-	0.0027	-

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